
2SB859

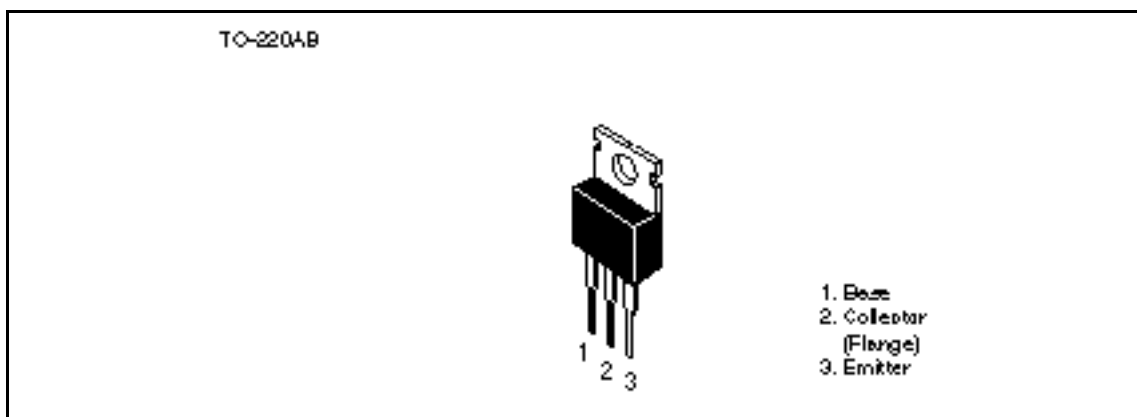
Silicon PNP Triple Diffused

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Application

Low frequency power amplifier complementary pair with 2SD1135

Outline



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-100	V
Collector to emitter voltage	V_{CEO}	-80	V
Emitter to base voltage	V_{EBO}	-5	V
Collector current	I_C	-4	A
Collector peak current	$I_{C(peak)}$	-8	A
Collector power dissipation	P_C^{*1}	40	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-45 to +150	°C

Note: 1. Value at $T_c = 25^\circ\text{C}$

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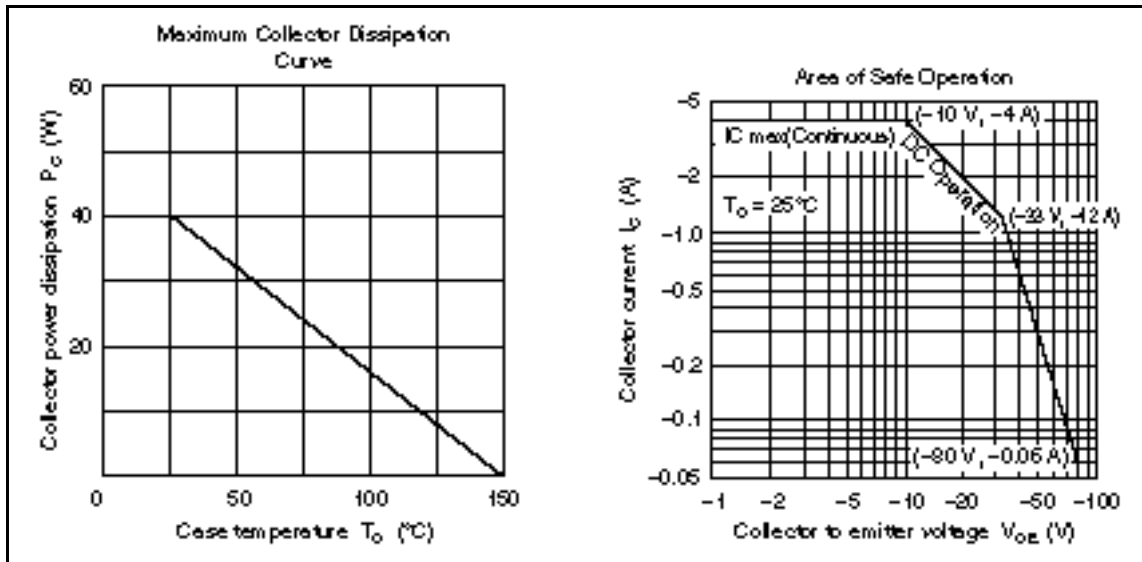
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-80	—	—	V	$I_C = -50 \text{ mA}$, $R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	V	$I_E = -10 \text{ } \mu\text{A}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-0.1	mA	$V_{CB} = -80 \text{ V}$, $I_E = 0$
DC current transfer ratio	h_{FE1}^{*1}	60	—	200		$V_{CE} = -5 \text{ V}$, $I_C = -1 \text{ A}^{*2}$
	h_{FE2}	35	—	—		$V_{CE} = -5 \text{ V}$, $I_C = -0.1 \text{ A}^{*2}$
Base to emitter voltage	V_{BE}	—	—	-1.5	V	$V_{CE} = -5 \text{ V}$, $I_C = -1 \text{ A}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-2	V	$I_C = -2 \text{ A}$, $I_B = -0.2 \text{ A}^{*2}$
Gain bandwidth product	f_T	—	20	—	MHz	$V_{CE} = -5 \text{ V}$, $I_C = -0.5 \text{ A}^{*2}$
Collector output capacitance	C_{ob}	—	75	—	pF	$V_{CB} = -20 \text{ V}$, $I_E = 0$, $f = 1 \text{ MHz}$

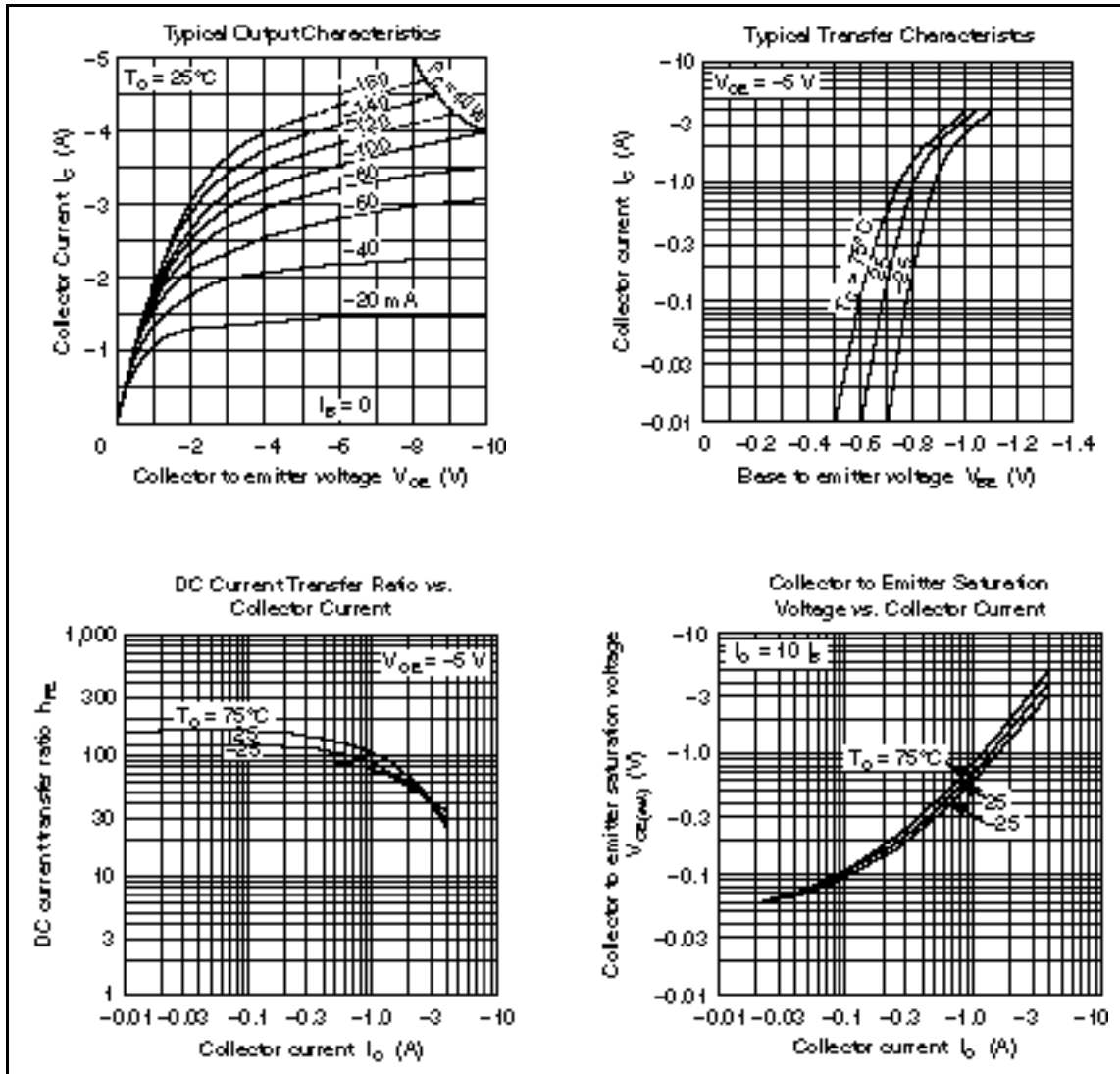
Notes: 1. The 2SB859 is grouped by h_{FE1} as follows.

2. Pulse test

B	C
60 to 120	100 to 200



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